arXiv:cond-mat/9507090v2 31 Jul 1995

Kondo Resonance in Transport Properties of Double Barrier Structure.

V.V.Ponomarenko

Frontier Research Program, RIKEN, Wako-Shi, Saitama 351-01, JAPAN.

Permanent address: A.F.Ioffe Physical Technical Institute,

194021, St. Petersburg, Russia.

I consider the effect of the finite width of the resonant level on its thermodynamics and tunneling transport properties in the single electron charging regime. The finite width of the levels results from their delocalization with formation of a narrow band due to their mutual overlap. Making use of $1/N$ technique one can show that there is a fixed energy level position at which the system undergoes the transition from the Kondo regime (above this energy) to the paramagnetic regime (below it). The linear bias conductance calculated as a function of the chemical potential turns out to be suppressed all around except for the vicinity of the transition energy where it has an asymmetrical resonant behavior.

PACS numbers: 73.40Gk, 73.20Dx, 72.15Qm

Typeset Using *REVTEX*

There is much interest in the study of low temperature transport in mesoscopic systems where new phenomena associated with quantum coherence are invoked by the large Coulomb charging energy of a localized constriction. These have been mostly discussed for the case of tunneling through a single spin-degenerate level specified with Anderson model [4]. Another way of manifesting a system with such a quantum correlation was recently suggested for a conducting granule in the Coulomb blockade condition [2], [5]. In these systems, in particular, the quasiclassical size of the granule results in the delocalization of the states and the appearance of a continuum band instead of the separate levels.

In this paper I will consider the effect of the delocalization of the resonant states on the Kondo resonance phenomenon dealing with the problem of tunneling through a double barrier (2D) structure (DBS) located between two conductors. This structure consists of the levels located at the impurity sites between the barriers. The sites are ordered into a lattice, and the levels of the neighbor cites have a small overlap, which leads to the appearance of a narrow band of width E_G. First, one could discuss this system as a vertical quantum dot structure where the tunneling layer is inside a constriction of radius R. This band should be considered continuous if its level splitting $\Delta_G \approx hv/R$ (v is the speed of the band electron with energy near the bottom) is less than the inverse time $\Gamma = \hbar/\tau$ of escape of the band electron into the electrodes. To make it more clear one could assume that this layer is infinite and the effective tunneling area through the layer is only of R^2 size. Then the probability for the tunneling electron to escape from this area along the layer could be estimated as relation between the squares of appropriate surfaces $2\pi Rv\tau$ and πR^2. This probability becomes negligible if $v\tau \ll R$.

The charging energy for accumulation of the charge Q inside the barriers could be evaluated in a standard way [6] as $Q^2/2C$ and decreases as R^2 due to dependence of the capacitance $C(R)$ on the area of the contact. Since the charging energy of a non-equilibrium distributed charge should be more than the one in equilibrium the criterion of a single-electron charging of the layer could be formulated as $R < l_C$ where $e^2/C(l_C) > \epsilon_b$, ϵ_b is the bottom of the impurity band. To evaluate possible parameters of such a system one could

use as an example the typical Metal-Oxide-Metal junction, where closely located conductors with the tunneling area of $100nm^2$ form a condensator with $\approx 100K$ charging energy. This value of the charging energy is substantially greater than the band width which, due to the previous restriction according to Γ, should be less than $0.1K$ for $10^2 - 10^3$ lattice sites. The dependence on R in this discussion could become irrelevant if the phase coherence length of the electrodes is less than R. I could generalize the consideration if I will suppose that this length satisfies the above two criteria instead of R.

Tunneling through the DBS is locally described by the Hamiltonian

$$H = \sum_k \epsilon_{a,k} c^+_{ks,a} c_{ks,a} + \sum_q \epsilon_q d^+_{qs} d_{qs} + \sum_{k,q,a,s} (V_{a,q,k} d^+_{qs} c_{ks,a} + V^*_{a,q,k} c^+_{ks,a} d_{qs}) \quad (1)$$

with a restriction on the Hilbert space that only states of zero $|0>$ and one-electron $|qs>$ occupation of the DBS band are permissible. Here $c_{ks,a}$ annihilates the electron of a lead with spin s in the state of wave vector $k = (k_\perp, k_\parallel)$ and of energy $\epsilon_{a,k}$. The components $k_\perp, k_\parallel$ are perpendicular and parallel to the layer, respectively. The operator d_{qs} annihilates an electron in the state localized inside the layer with spin s, and wave vector q, and energy ϵ_q. An expression for the tunneling matrix elements $V_{a,q,k}$ could be generally written making use of the tight binding model for the DBS band as

$$V_{a,q,k} = \frac{1}{ML^{1/2}} \sum_j T_{aj}(k_\perp) exp(iR_j q - i\phi_{aj}(k_\parallel)) \quad (2)$$

Here M is the effective number of the sites of the layer restricted either by the geometry or by the coherence length. L is the normalization in the direction perpendicular to the layer, and T_{aj} is the modulus of the corresponding tunneling amplitude. The vertex function may be introduced as $\Gamma_{a,\omega}(q_1, q_2) = \pi \sum_k \delta(\omega - \epsilon_k) V^*_{a,q_1,k} V_{a,q_2,k}$ which is completely ample for our future needs. Moreover, in the low temperature limit only the transitions between the holes of the Fermi surface ($\omega \approx 0$) and the electrons of the bottom of the layer band are important. (I will suppose that the bottom is reached at $\epsilon_{q=0} = \epsilon_b$.) To calculate the function in this limit one could exploit either the jelly model for the leads or the tight binding model if all structure are commensurate. Virtually, the result is the same in the above limit. Indeed, taking $\phi_{ja} = R_j k_\parallel$ one finds

$$\Gamma_{a,\omega}(q_1,q_2)=\pi\sum_{Q,Q'}\delta_{k_\parallel,q_1+Q}\delta_{k_\parallel,q_2+Q'}\int d\epsilon_{k_\perp}\rho_{1D}(\epsilon_{k_\perp})\delta(\omega-\epsilon_{k_\perp}-\epsilon_{k_\parallel})T_a^2(\epsilon_{k_\perp})\simeq\pi T_a^2\rho_{a,1D}(0)\delta_{q_1,q_2} \tag{3}$$

where Q,Q' are the vectors of the reciprocal lattice either of the DBS or of the leads. T_{aj} is taken as a constant if the position of the j DBS site corresponds to the position of the lead site (and in the case of the jelly model). Otherwise, it was put zero. The second equation in (3) is correct if the DBS lattice is less close than the lattice of the leads. If this condition is not met, the transitions between nonequal q_1,q_2 become permissible. I will not discuss it specially, though, the consideration could be easy generalized to account for them.

Conservation of the q components in (3) makes the tunneling resonant and justifies the application of the $1/N$ expansion technique [1]. In this case it is a $1/M$ expansion and it means the summing up of the most divergent terms in M of each order of expansion in Γ. I will restrict my consideration to leading order, giving summation of all terms of $(\Gamma M)^n$.

Starting from the thermodynamics I will include the DBS contribution into the partition function in terms of the self energy of the slave-boson $\Sigma_0(z)$ [1]. To leading order it takes the form

$$\frac{Z^{(1)}}{Z_{band}}=\sum_{q,s}e^{-\beta\epsilon_q}+\int_C\frac{dz}{2\pi i}e^{-\beta z}\frac{1-\partial_z\Sigma_0^{(1)}(z)}{z-\Sigma_0^{(1)}(z)} \tag{4}$$

where C encircles all the singularities of the integrand, $\beta=1/T$ is the inverse temperature, and $\Sigma_0^{(1)}(z)$ is given by

$$\Sigma_0^{(1)}(z)=\sum_{a,s,q}\int_{-E_F}^{\infty}d\omega\Gamma_a\frac{f(\omega)}{z-\epsilon_q+\omega} \tag{5}$$

In the low temperature limit the Fermi-Dirac function $f(\omega)$ can be approximate by the step function. Then $\Sigma_0^{(1)}$ for 2D band, which has a constant density of states $\rho_{2D}=m^*/(2\pi\hbar^2)$ near the edge, is

$$\Sigma_0^{(1)}(z)=\Delta\epsilon_b+P[E_G ln\frac{E_G+\epsilon_b-z}{E_G}+(\epsilon_b-z)ln\frac{E_G+\epsilon_b-z}{\epsilon_b-z}] \tag{6}$$

where $P=2(\Gamma/\pi)\rho_{2D}S\simeq(\Gamma/\pi)M/E_G,\Gamma=\sum_a\Gamma_a,S$ is the square of the tunneling surface, $\Delta\epsilon_b=PE_G(ln(E_G/E_F)-1)$. P is a number of the states lying inside the energy interval

of width Γ/π. In the above condition $P \gg 1$. This function (6) coincides with the one of a single level Kondo model for $|\epsilon_b - z| \gg E_G$. However, for small $|\epsilon_b - z|$ its behavior is quite different. In particular, the self-energy $\Sigma_0^{(1)}(z)$ converges to the finite negative value $\Delta\epsilon_b$ at ϵ_b and acquires an imaginary part on the real axis above ϵ_b as $Im\Sigma_0^{(1)}(x - i0) = \pi P(x - \epsilon_b)$.

This means that unless ϵ_b becomes lower then $\Delta\epsilon_b$, the lowest singularity of the integrand in (4) is a simple pole $z = \epsilon_b - T_K$, which corresponds to the bound state of the slave-boson with energy $T_K \equiv E_G x$

$$\frac{\bar{\epsilon_b}}{PE_G} = ln(1+x) + xln(1+x^{-1}) + \frac{x}{P}, \qquad \bar{\epsilon_b} = \epsilon_b - PE_G(ln(E_G/E_F) - 1) \tag{7}$$

In the limit $\epsilon_b/|\Delta\epsilon_b| \ll 1$ the solution of (7) loses its dependence on ϵ_b and shows that $T_K \simeq |\Delta\epsilon_b|$ when $E_F \gg E_G$. In the more general case $\bar{\epsilon_b}$ could reach the zero, where the transition into a paramagnetic state of the DBS occurs. In that regime the low temperature thermodynamics of the DBS is ruled out by the lowest states of its band.

The standard way of calculating [3] the localized charge n_G, the charge χ_C and the spin χ_s susceptibilities results, for the Kondo regime behavior in

$$\begin{aligned} F_{DBS} = -Tln\left[\frac{Z^{(1)}}{Z_{band}}\right] = \epsilon_b - T_K, \quad n_G = \frac{\partial F_{DBS}}{\partial \epsilon_b} = 1 - Z_0 \\ \chi_C = -\frac{PE_G Z_0^3}{T_K(E_G + T_K)} \quad , \quad \chi_s = \frac{PE_G Z_0}{8T_K(E_G + T_K)} \\ Z_0 = \frac{1}{1 - \partial_z \Sigma_0(z)|_{z=\epsilon_b - T_K}} = \frac{1}{1 + Pln[(E_G + T_K)/T_K]} \end{aligned} \tag{8}$$

The temperature dependence is dropped in Eq. (8). It remains unimportant while $PT/\Gamma \ll exp(T_K/T)$. These solutions (7, 8) predict the singular behavior of all thermodynamic characteristics at $\bar{\epsilon_b} = 0$. The function n_G goes to 1 as $1/ln(\bar{\epsilon_b}/E_G)$.

In the paramagnetic regime the low temperature asymptotic for (4) is

$$\begin{aligned} \frac{Z^{(1)}}{Z_{band}} = \frac{MT}{E_G} e^{-\epsilon_b/T} a(\epsilon_b, T) \\ a = 1 - \beta \int_0^\infty dx \frac{\Gamma}{\pi} \frac{\bar{\epsilon_b} + Px}{(\bar{\epsilon_b} + Px(1 + ln(E_G/x)))^2 + (\pi P x)^2} \end{aligned} \tag{9}$$

If $-\bar{\epsilon_b} > TPln(E_G/T)$ the parameter a is evaluated as $a = 1 - \Gamma/(\pi\bar{\epsilon_b})$. From Eq. (9) one concludes that $n_G = 1$ and χ_s diverges as $1/T$.

Discussing the transport through this structure I will restrict consideration to linear conductance. Then, the conductance can be expressed in terms of the imaginary part of the retarded Green function [7] of the DBS electrons $G_q(\omega)$ labelled with the quasi momentum q and energy ω indices. Up to T^2 corrections it is given by

$$\sigma_0 = -\frac{2e^2}{\hbar}\frac{\Gamma_R\Gamma_L}{\Gamma^2}P\sum_s \int d\epsilon_q ImG_q(\omega)|_{\omega=0} \tag{10}$$

In this technique the full Green function of electron is calculated as a convolution [1] of the slave-boson and the slave-fermion Green functions along the appropriate contour in the complex energy plane. For the imaginary part it is simplified to

$$ImG_q(\omega_+) = -\frac{1}{Z/Z_{band}}\int_\infty^\infty \frac{dx}{\pi}\frac{Im\Sigma_0(x_+)Im\Sigma_q(x+\omega_+)}{|x-\Sigma_0(x_)|^2|x+\omega-\epsilon_q-\Sigma_q(x+\omega)|^2}(1+e^{-\beta\omega})e^{-\beta x} \tag{11}$$

Here $\Sigma_q(x_+)$ is the self energy of the slave fermion which is taken at the real point $x_+ = x+i0$ with the infinitely small imaginary shift.

In the Kondo regime the calculations straightforwardly follow the ones of the single level case. To leading order in the $1/M$ expansion, the imaginary parts of both the slave boson and the slave fermion Green functions become strongly localized as $Z_0\delta(\omega - T_K)$ and $\delta(\omega-\epsilon_q)$, respectively, at low temperatures by the factor $exp(-T/T_K)$. To obtain a non-zero $ImG_q(0)$ I should use the next order expression for $Im\Sigma_q(x)$ standing in the numerator of (11). This is written as

$$Im\Sigma_q(y_+) = Im\frac{\Gamma}{\pi}\int \frac{dx}{y-x-\Sigma_0^{(1)}(y_+-x)} = -\Gamma Z_0(1-f(y-\epsilon_b+T_K)) \tag{12}$$

for $y<\epsilon_b$. Finally, I obtain

$$ImG_q(\omega_+) = -\frac{\Gamma Z_0^2}{(\omega-\epsilon_q+\epsilon_b-T_K)^2}, \quad \sigma_0 = \frac{4e^2}{\hbar}\frac{\Gamma_R\Gamma_L}{\Gamma^2}\frac{PZ_0^2E_G}{T_K(T_K+E_G)} \tag{13}$$

Taking T_K from Eq.(7) and Z_0 from Eq.(9) one finds

$$\sigma_0 = \frac{2e^2}{\hbar}\frac{\Gamma_R\Gamma_L}{\Gamma^2}\frac{\Gamma}{\pi\bar{\epsilon_b}ln(E_G/\bar{\epsilon_b})} \tag{14}$$

for small T_K. This shows that the resonance in the σ_0 dependence on the bottom energy is reached at $\epsilon_b = \Delta\epsilon_b$, and it decreases with increasing $\bar{\epsilon_b}$ more slowly than the $1/\bar{\epsilon_b}^2$ tail of

the one electron resonance. The width on this side of the resonance is less than Γ in the factor $1/ln(E_G/\Gamma)$. Eq. (13) is applicable only far from the resonance. Near the resonance it could be corrected with the summation of the infinite series of the $1/M$ expansion as the NCA does.

In the paramagnetic phase, when ϵ_b lies below $\Delta\epsilon_b$, the imaginary parts of the self energies give a contribution into the conductance already in the leading order. However, this contribution is $\propto T$ since $\Sigma_0^{(1)}(y) \propto (y-\epsilon_b)$. The zero temperature part of σ_0 appears if the imaginary part of Σ_0 standing in the numerator of (11) is taken in the next order. Then it is equal to

$$\Sigma_0^{(2)}(z) = P\frac{\Gamma}{\pi}\int_{-E_F}^{0} d\epsilon[\frac{1}{z+\epsilon-\epsilon_b-E_G} - \frac{1}{z+\epsilon-\epsilon_b}]\int_0^{E_F}\frac{d\epsilon'}{z+\epsilon-\epsilon'-\Sigma_0^{(1)}(z+\epsilon-\epsilon')} \quad (15)$$

Extracting from here the imaginary part and collecting the leading terms one could find

$$\sigma_0 = \frac{8e^2}{\hbar}\frac{\Gamma_R\Gamma_L}{\Gamma a\bar{\epsilon_b}^2}P(\Gamma\frac{\phi(\bar{\epsilon_b})}{\pi}+T) \quad (16)$$

for $T < |\bar{\epsilon_b}|/(Pln\frac{E_G}{|\bar{\epsilon_b}|})$. The coefficient ϕ is given by

$$\phi(\bar{\epsilon_b}) = -\int_0^{E_F}\frac{d\epsilon}{\epsilon_b-\epsilon-\Sigma_0^{(1)}(\epsilon_b-\epsilon)} \simeq \frac{1}{P}lnln(\frac{E_GP}{|\bar{\epsilon_b}|}) + ln(\frac{PE_G}{E_F+PE_G}) \quad (17)$$

Equation (16) describes the decay of the resonance below $\epsilon_b = \Delta\epsilon_b$. It reveals that the square of the halfwidth is larger than Γ^2 by a factor $P\phi$.

Finally, one could conclude that the delocalization of the resonant levels with formation of a narrow band which is located inside the barrier in between two electrodes, leads to the suppression of the Kondo conductance all around except for a special position of the level energies at $\epsilon_b = PE_G(ln(E_G/E_F)-1)$. At this point the tunneling structure contributions to the thermodynamic functions become singular, and the linear conductance has a resonant behavior. These results are easy related to the known properties of the Coulomb blockade transport through the granule [6]. The above consideration describes the first steps of the Coulomb staircase. Due to the lack of the electron-hole symmetry in the excitation spectrum of the granule the position of the resonance is shifted from $n_G = 1/2$ [2] to $n_G = 1$, and the form of the resonance undergoes asymmetrical deformation [5].

I am grateful to D. Averin and K. K. Likharev for elucidative discussions during my staying in Stony Brook, and M. Stopa for his interest and kind help, and RIKEN ICO for the hospitality. This work was supported by the STA Fellowship (Japan) and by ONR grant 00014-93-1-0880.

REFERENCES

[1] N.E. Bickers, Rev. Mod. Phys. **59**,845 (1987).

[2] K.A.Matveev, Zh. Eksp. Teor. Phiz. **99**, 1598 (1991) [Sov. Phys. JETP **72**, 892 (1991)].

[3] A. C. Hewson, *The Kondon Problem to Heavy Fermions* (Cambridge Univ. Press, Cambridge, England, 1993).

[4] L.I. Glazman and M. E. Raikh, Pis'ma Zh. Eksp. Teor. Phiz. **47**, 378 (1988) [JETP Lett. **47**, 452 (1988)]; Y. Meir, N.S. Wingreen and P.A. Lee, Phys. Rev. Lett. **70**, 2601 (1993); T.K. Ng , Phys. Rev. Lett. **70**, 1768 (1993).

[5] H. Schoeller and G. Schon, Phys. Rev. B **50**, 18436 (1994).

[6] D. Averin and K. K. Likharev, in *Mesoscopic Phenomena in Solids* , edited by B. L. Altshuller *et al* (Elsevier, Amsterdam, 1991), p.173.

[7] L.I. Chen and C.S. Ting, Phys. Rev. B **41**, 8533 (1990); Y. Meir and N.S. Wingreen, Phys. Rev. Lett. **68**, 2512 (1992).